



**PFAS-free products -
we pay attention**

*micro resist
technology*

Positive Photoresists



Ready-to-use high performance photoresists for standard UV, greyscale, and laser interference lithography

- Excellent process compatibility
- Variety of viscosities
- No post exposure bake required
- Easy removal
- RoHS compliance
- Production according to ISO 9001 and ISO 14001
- PFAS-free

- Made in Germany -

micro resist technology GmbH

Gesellschaft für chemische Materialien spezieller Photoresistsysteme mbH

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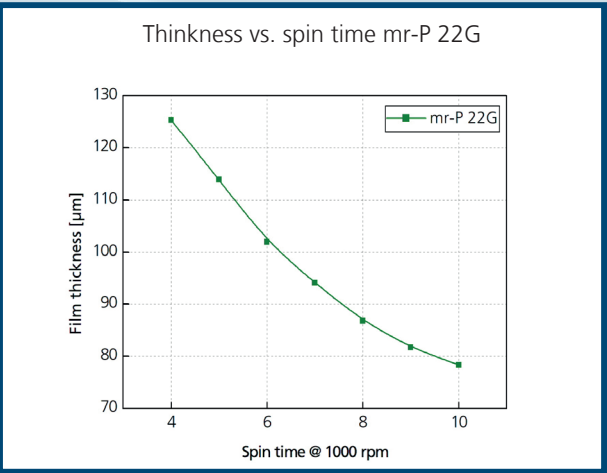
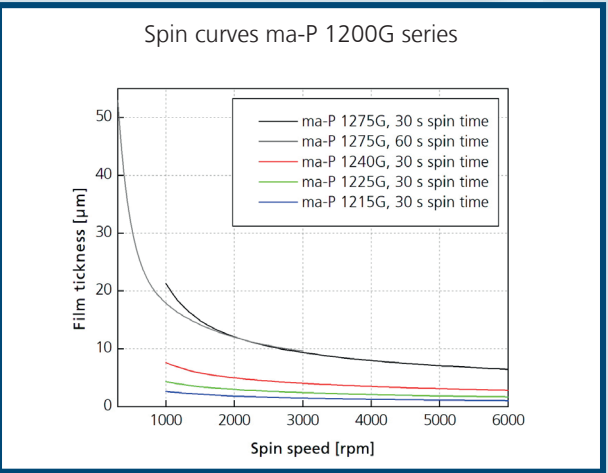
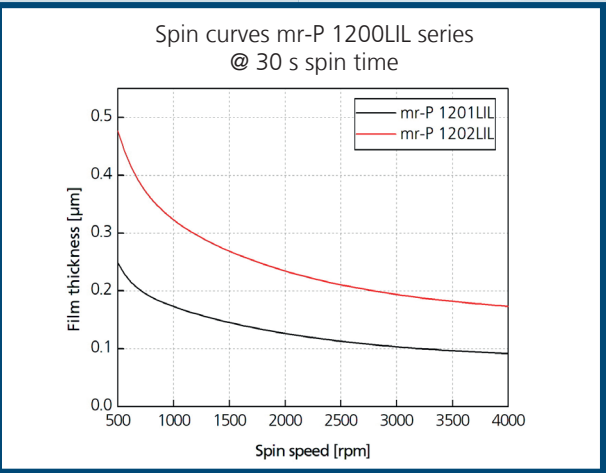
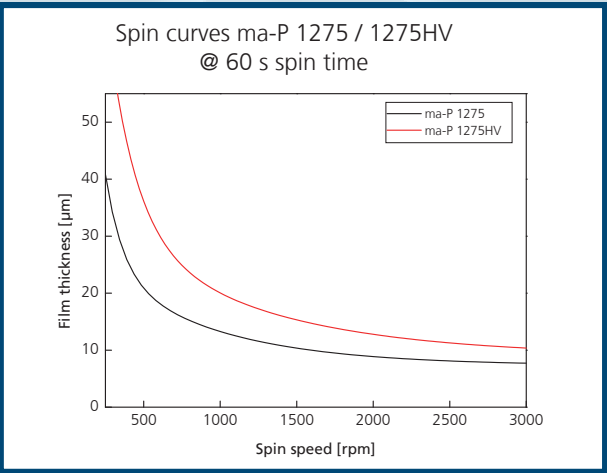
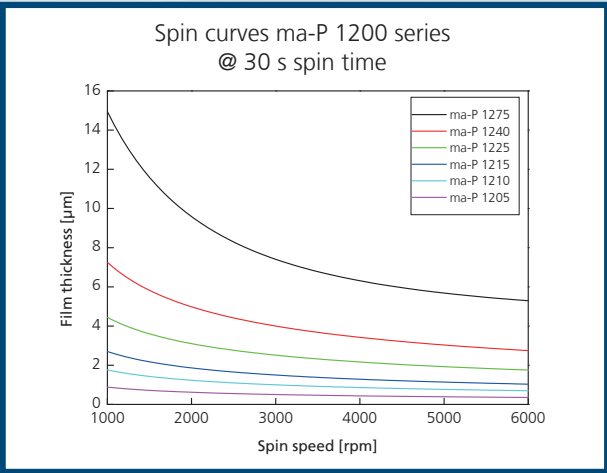
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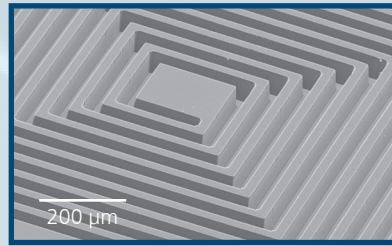
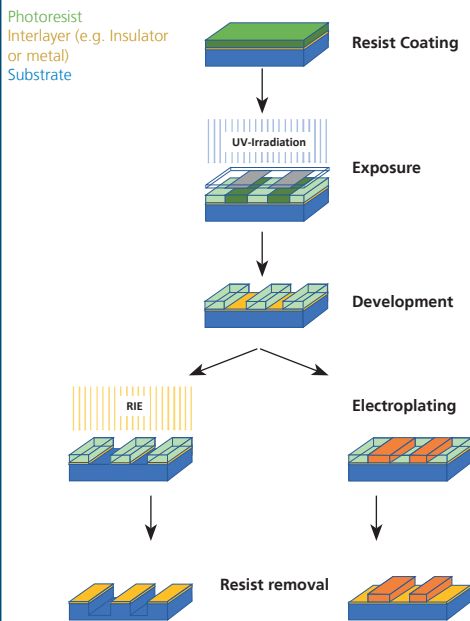
Properties and key parameters													
Resist	Patterning method					Spectral sensitivity	Typical film thickness			Developer			Pattern transfer methods
	Standard UV lithography		Grey scale lithography		Laser interference lithography (LIL)		Spin coating @3000rpm	max. film thickness	Available types ¹⁾	TMAH based	NaOH based	Silicate / phosphate based	
		+ subsequent reflow	Direct write lithography (DWL)	Mask		[nm]	[µm]	[µm]					
ma-P 1200 series	x	x				330 - 450	0.5 1.0 1.5 2.5 4.0 7.5		ma-P 1205 ma-P 1210 ma-P 1215 ma-P 1225 ma-P 1240 ma-P 1275	mr-D 526/S	ma-D 331 ma-D 331/S		Dry and wet etching, Electroplating, Ion implantation, Master for thermal (e.g. PDMS) and UV moulding (e.g. OrmoStamp®FF) from reflowed patterns
ma-P 1275HV	x	x				350 - 450	11	60 - 70		mr-D 526/S	ma-D 331 ma-D 331/S		
mr-P 1200LIL series					x	330 - 450	0.1 0.2		mr-P 1201LIL mr-P 1202LIL			ma-D 374/S	Dry and wet etching
ma-P 1200G series	x	x	x	x	x	350 - 450	1.5 2.5 4.0 9.5	60 ²⁾ 120 ³⁾	ma-P 1215G ma-P 1225G ma-P 1240G ma-P 1275G	mr-D 526/S ⁴⁾	ma-D 331 ⁵⁾		Master for thermal (e.g. PDMS) and UV moulding (e.g. OrmoStamp®FF), Electroplating
mr-P 22G			x very deep	(x)	x	330 - 420	17	120 - 140 ²⁾ 170 - 200 ³⁾		mr-D 526/S (ma-D 532/S)			

¹⁾ Additional custom-specific types available upon request ²⁾ single coating ³⁾ double coating ⁴⁾ for greyscale lithography ⁵⁾ for binary lithography

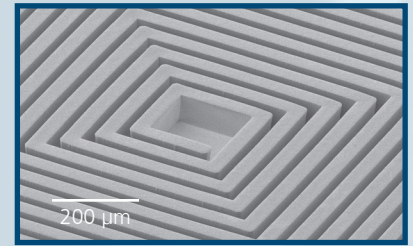


enabled by ready-to-use formulations

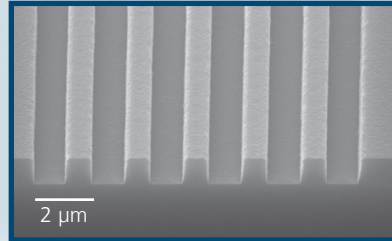
Process flow RIE / Electroplating



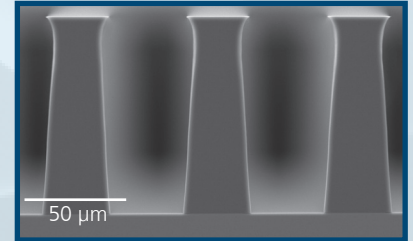
56 µm thick ma-P 1275HV mould



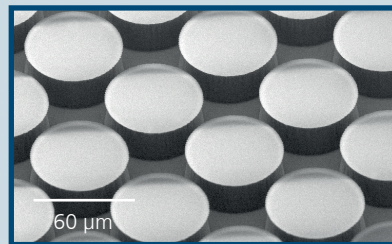
48 µm thick electroplated Ni



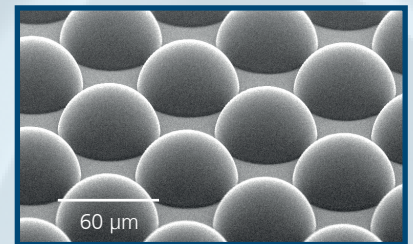
0.8 µm lines in 1.0 µm thick ma-P 1210



30 µm lines in 100 µm thick ma-P 1275G

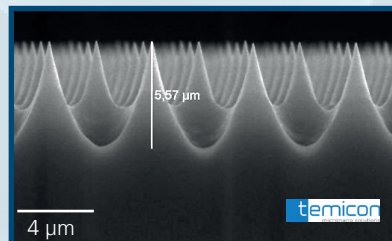
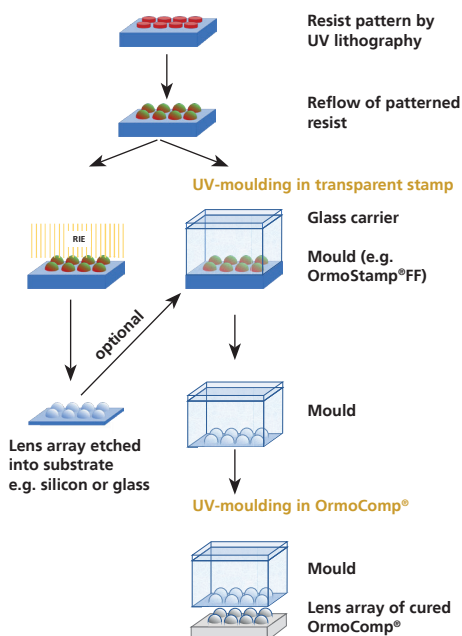


20 µm high ma-P 1275, 60 µm diameter pillars

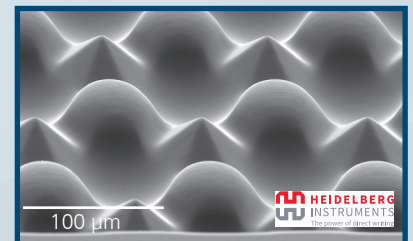


30 µm high reflowed ma-P 1275, 60 µm diameter

Process flow Reflow of ma-P 1200 / ma-P 1200G and pattern transfer



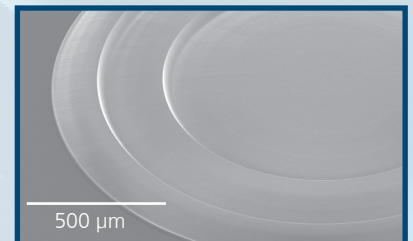
Moth eye pattern in 10 µm thick ma-P 1275G patterned by LIL @ 351 nm



Convex and concave hexagonal lenses, 60 µm diameter in ma-P 1275G

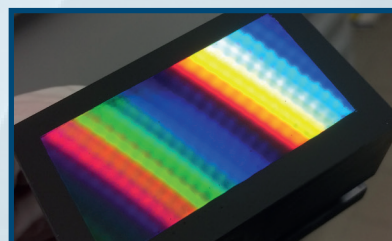
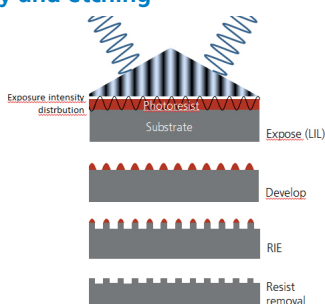


63 µm deep pattern in ma-P 1275G, patterned by Heidelberg Instruments

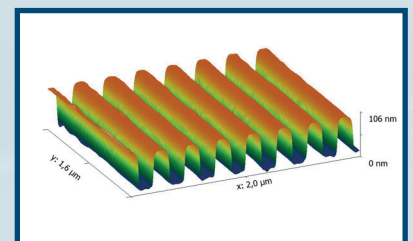


Fresnel lens, 2 mm diameter, 42 µm depth, patterned in ma-P 1275G

Process flow Laser Interference Lithography and etching



Diffractive optic: laminar grating (50 x 30 mm²) in mr-P 1202LIL



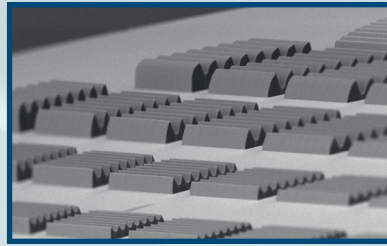
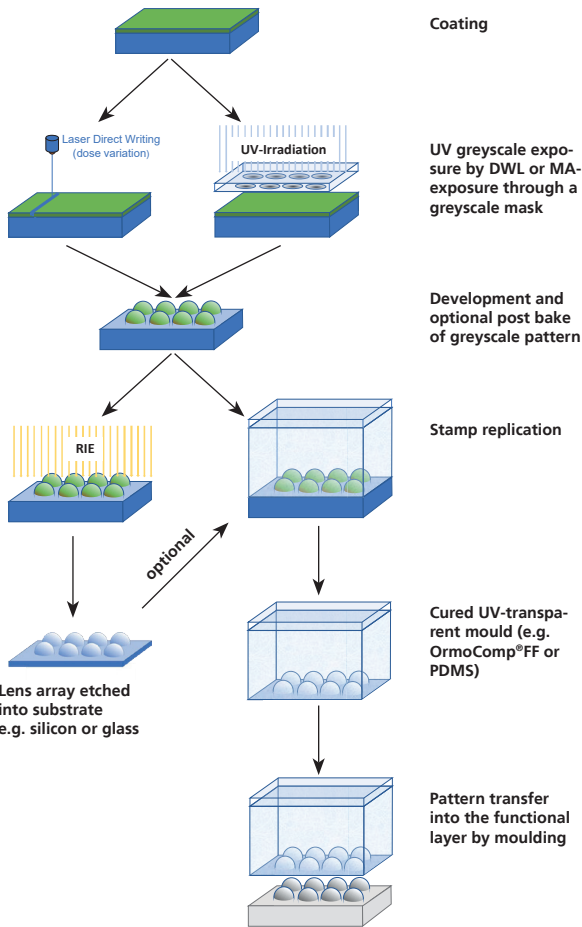
100 nm thick mr P 1201LIL, 125 nm pattern width

Positive Photoresists

e.g. for 2.5D applications

Process flow

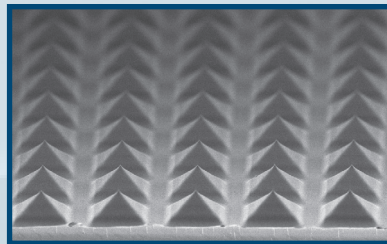
Greyscale Lithography and pattern transfer



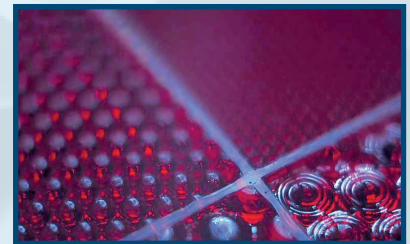
MA exposure with 405 nm filter, HEBS glass greyscale mask (by Canyon Materials Inc.): max. 70 μm high saw tooth patterns in different heights and pitches



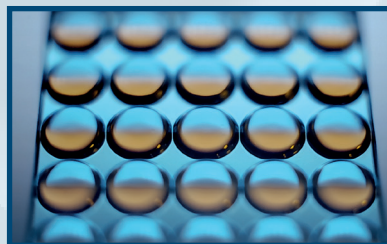
103 μm high, 2 mm diameter Fresnel lens¹⁾ (DWL66+)



DWL @ $\lambda = 355 \text{ nm}$
Pyramids, 10 μm base width, 5 μm height, 45° angle²⁾



DWL @ $\lambda = 405 \text{ nm}$
with PICOMASTER XF 200: 125 μm high lenses, and Fresnel lenses 125-500 μm diameter³⁾



DWL @ $\lambda = 405 \text{ nm}$ (DWL 66+):
70 μm high, 500 μm diameter lenses¹⁾

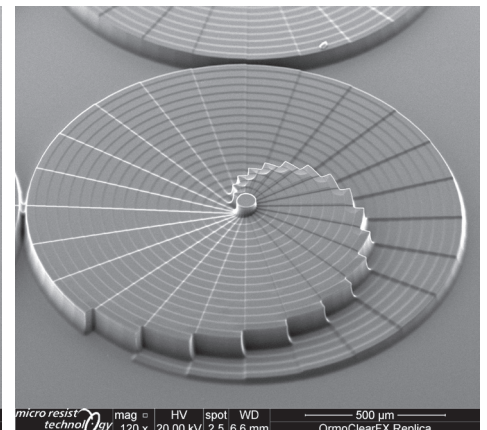
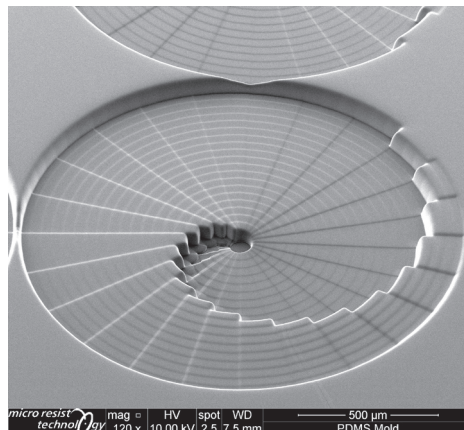
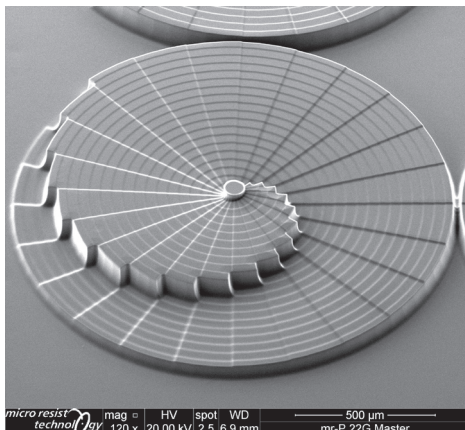


Greyscale pattern by DWL
@ $\lambda = 405 \text{ nm}$ (DWL 66+)¹⁾

patterning and pictures by courtesy of
¹⁾ Heidelberg Instruments Mikrotechnik GmbH
²⁾ IMS CHIPS
³⁾ RAITH laser systems

Pattern transfer by UV moulding

Process flow Pattern transfer (example)



130 μm deep mr-P 22G pattern



Thermal moulding with PDMS

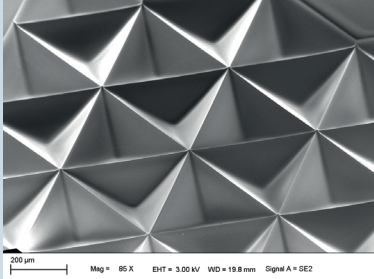


UV moulding with OrmoClear®FX

Positive Photoresists

Highlights and inspirations

Highlight: Thick Film Positive Photoresist for Greyscale Lithography - **mr-P 22G**



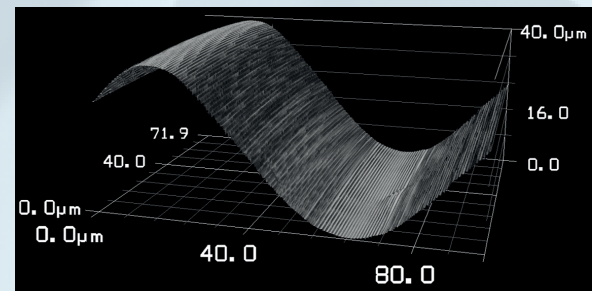
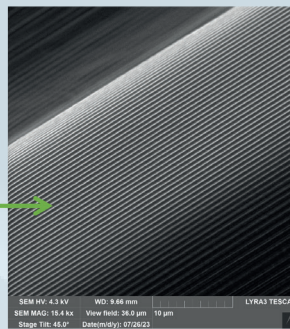
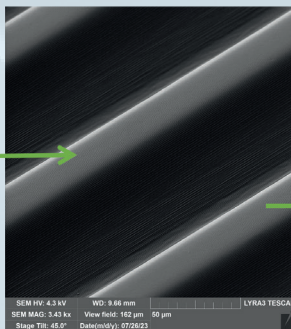
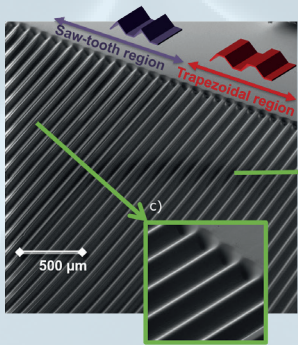
DWL @ $\lambda = 405$ nm with DWL 66+:
155 μm deep tetrahedrons
patterning and pictures by courtesy of
Heidelberg Instruments Mikrotechnik GmbH

Main features

- ⇒ Specifically designed for the requirements of greyscale lithography in up to 200 μm thick films for up to 140–160 μm deep greyscale patterns
- ⇒ Very low residual absorption after exposure enables up to 140–160 μm pattern depth in greyscale lithography
- ⇒ Suitable exposure wavelengths: $\lambda = 330\text{--}420$ nm ($\lambda = 405$ nm and higher suited for deep patterns)
- ⇒ Aqueous alkaline development with TMAH based developers

Experimental approaches:

ma-P 1275G for hierarchical patterns by mix&match (combining DWL & LIL)



- ⇒ Large structure (405 nm - DWL manufactured);
100 μm grating period, 40 μm depth
- ⇒ Small structure (405 nm - LIL manufactured);
690 nm grating period, ~ 400 nm depth

- ⇒ Optical pattern assessment:
405 nm - LIL manufactured surface gratings on different parts of the
405 nm - DWL fabricated wave pattern in ma-P 1275G

patterning and pictures by courtesy of Joanneum Research and University of Žilina



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